unit: mm

2.9±0.2

2.6±0.1

.55±0.15

4.6±0.2

1.4±0.2

1.6±0.2

9.9+0

1.2±0

13.7±0.2 Dip

2SK3042

Silicon N-Channel Power F-MOS FET

Features

- Avalanche energy capacity guaranteed: EAS > 45mJ
- High-speed switching: $t_f = 30$ ns
- No secondary breakdown

Applications

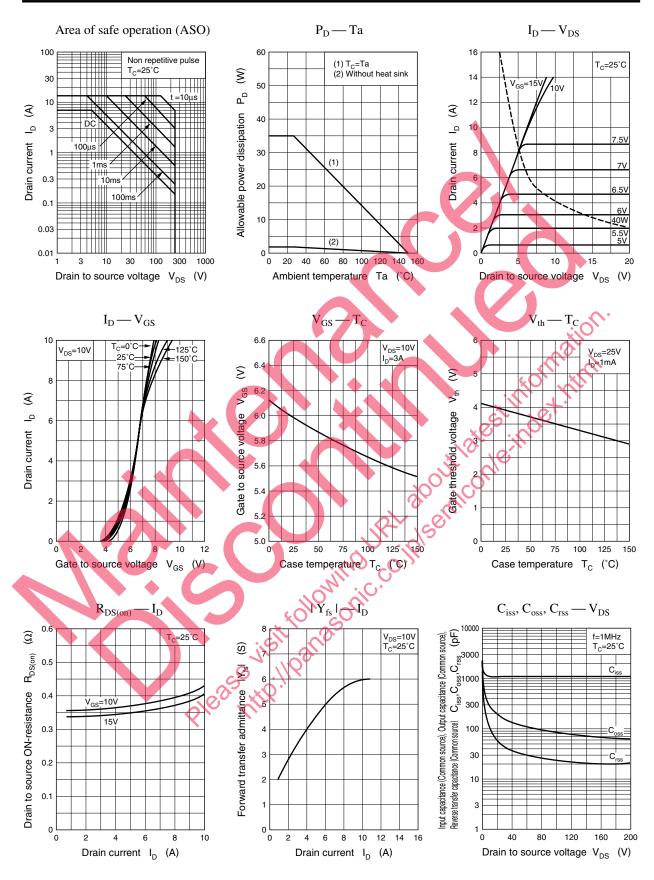
- Contactless relay
- Diving circuit for a solenoid
- Driving circuit for a motor
- Control equipment
- Switching power supply

Absolute Maximum Ratings ($T_c = 25^{\circ}C$)

Parameter		Symbol	Ratings	Unit
Drain to Source breakdown voltage		V _{DSS}	250	V
Gate to Source voltage		V _{GSS}	±20	V
Drain current	DC	I _D	±7	A
	Pulse	I _{DP}	±14	A
Avalanche energy capacity		EAS*	45	mJ
Allowable power	$T_C = 25^{\circ}C$	P _D	35	W
dissipation	$Ta = 25^{\circ}C$	1 D	2	~~
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to +150	°C
* $L = 0.1 \text{ mH}, I_L = 8.1 \text{ mH}$	A, $V_{DD} = 50V$, 1 pulse		

Electrical Characteristics ($T_c = 25^{\circ}C$)

* L = 0.1mH, $I_L = 8A$, $V_{DD} = 50V$, 1 pulse											
* L = 0.1mH, I_L = 8A, V_{DD} = 50V, 1 pulse Electrical Characteristics (T_C = 25°C)											
Parameter	Symbol	Conditions	min	typ	max	Unit					
Drain to Source cut-off current	I _{DSS}	$V_{DS} = 200V, V_{GS} = 0$			0.1	mA					
Gate to Source leakage current	I _{GSS}	$V_{GS} = \pm 20 V, V_{DS} = 0$			±1	μA					
Drain to Source breakdown voltage	V _{DSS}	$I_D = 1$ mA, $V_{GS} = 0$	250			V					
Gate threshold voltage	Vth	$V_{DS} = 10V, I_D = 1mA$	1		5	V					
Drain to Source ON-resistance	R _{DS(on)}	$V_{GS} = 10V, I_D = 5A$		0.4	0.6	Ω					
Forward transfer admittance	Y _{fs}	$V_{DS} = 10V, I_D = 5A$	2.7	4.7		S					
Diode forward voltage	V _{DSF}	$I_{DR} = 8A, V_{GS} = 0$			-1.7	V					
Input capacitance (Common Source)	C _{iss}			1100		pF					
Output capacitance (Common Source)	C _{oss}	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$		200		pF					
Reverse transfer capacitance (Common Source)	C _{rss}			60		pF					
Turn-on time (delay time)	t _{d(on)}			20		ns					
Rise time	t _r	$V_{GS} = 10V, I_D = 5A$		20		ns					
Turn-off time (delay time)	t _{d(off)}	$V_{DD} = 100 \text{V}, \text{R}_{\text{L}} = 20 \Omega$		130		ns					
Fall time	t _f			30		ns					





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